

HEFEI HEJING ELECTRONICS CO.LTD

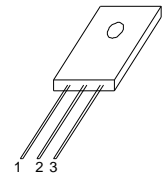
HJ 13003

NPN EPITAXIAL SILICON

TRANSISTOR

Absolute Maximum Ratings (Ta=25)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	700	V
Collector-Emitter Voltage	V_{CE0}	400	V
Emitter-Base Voltage	V_{EB0}	9	V
Collector Current	I_C	1	A
Collector Power Dissipation	P_C	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~ 150	



1, B 2, C 3, E

TO-126

Electrical Characteristic (Ta=25)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Voltage	V_{CB0}	$I_C=1mA$	700			V
Collector-Emitter Voltage	V_{CE0}	$I_C=10mA$	400			V
Emitter-Base Voltage	V_{EB0}	$I_E=1mA$	9			V
DC Current Gain	h_{FE}	$V_{CE}=10V, I_C=0.5A$	10		40	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1A$ $I_B=0.25A$			1	V

h_{FE} Classification: 10~ 15 15~ 20 20~ 25 25~ 30
 30~ 35 35~ 40